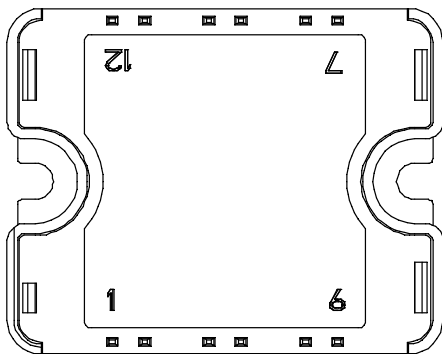
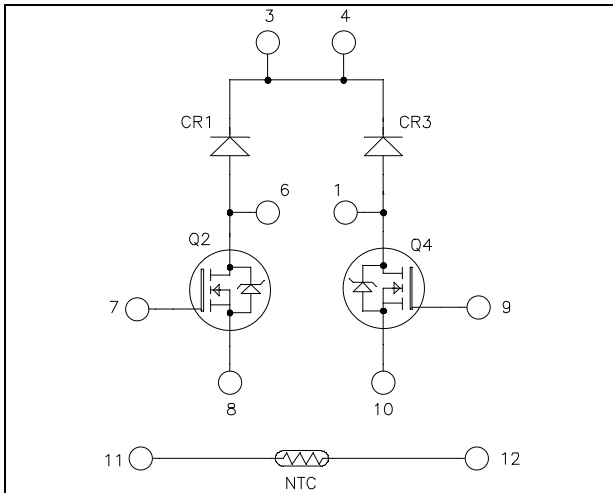


**Dual boost chopper
Super Junction MOSFET
Power Module**

$V_{DSS} = 600V$
 $R_{DSon} = 45m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 49A \text{ @ } T_c = 25^\circ C$



Pins 3/4 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features



- Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
 - Very low stray inductance
 - Symmetrical design
 - Internal thermistor for temperature monitoring
 - High level of integration
- ### Benefits
- Outstanding performance at high frequency operation
 - Direct mounting to heatsink (isolated package)
 - Low junction to case thermal resistance
 - Solderable terminals both for power and signal for easy PCB mounting
 - Each leg can be easily paralleled to achieve a single boost of twice the current capability
 - Low profile
 - RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	49
		$T_c = 80^\circ C$	38
I_{DM}	Pulsed Drain current	130	A
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	45	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	250
I_{AR}	Avalanche current (repetitive and non repetitive)	15	A
E_{AR}	Repetitive Avalanche Energy	3	mJ
E_{AS}	Single Pulse Avalanche Energy	1900	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$			250	μA
		$T_j = 25^\circ\text{C}$				
		$V_{GS} = 0V, V_{DS} = 600V$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 24.5A$		40	45	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3\text{mA}$	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 25V$ $f = 1\text{MHz}$		7.2		nF
C_{oss}	Output Capacitance			8.5		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 300V$ $I_D = 49A$		150		nC
Q_{gs}	Gate – Source Charge			34		
Q_{gd}	Gate – Drain Charge			51		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 49A$ $R_G = 5\Omega$		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			100		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 10V ; V_{Bus} = 400V$ $I_D = 49A ; R_G = 5\Omega$		675		μJ
E_{off}	Turn-off Switching Energy			520		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 10V ; V_{Bus} = 400V$ $I_D = 49A ; R_G = 5\Omega$		1100		μJ
E_{off}	Turn-off Switching Energy			635		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		25	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current			60		A
V_F	Diode Forward Voltage	$I_F = 60A$		1.7	2.3	V
		$I_F = 120A$		2		
		$I_F = 60A$	$T_j = 125^\circ\text{C}$	1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60A$ $V_R = 400V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	70		ns
			$T_j = 125^\circ\text{C}$	140		
Q_{rr}	Reverse Recovery Charge	$I_F = 60A$ $V_R = 400V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		nC
			$T_j = 125^\circ\text{C}$	690		

Thermal and package characteristics

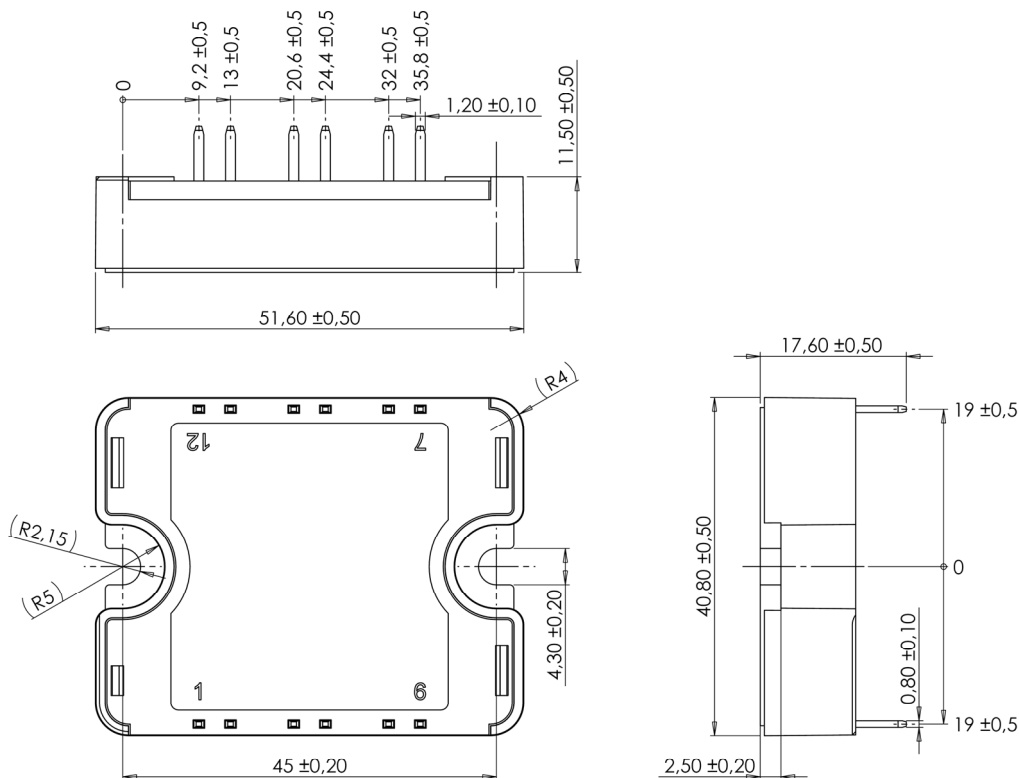
Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	CoolMOS		0.5	°C/W	
		Diode		0.85		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

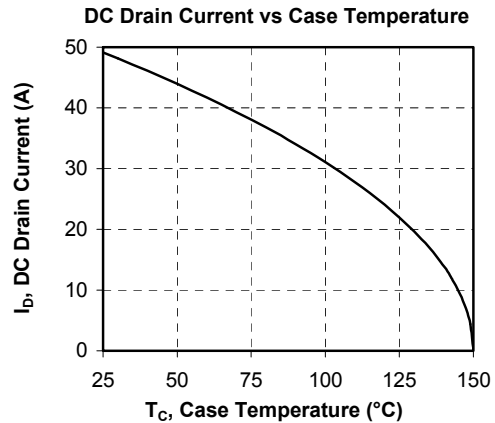
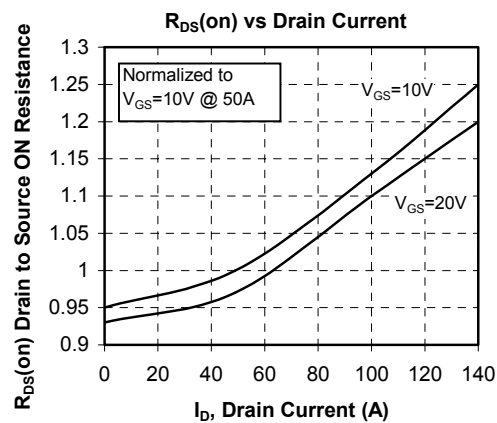
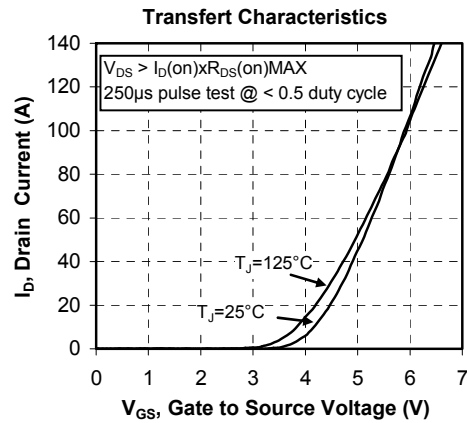
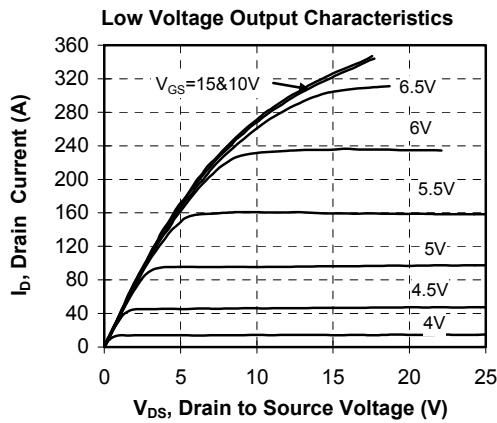
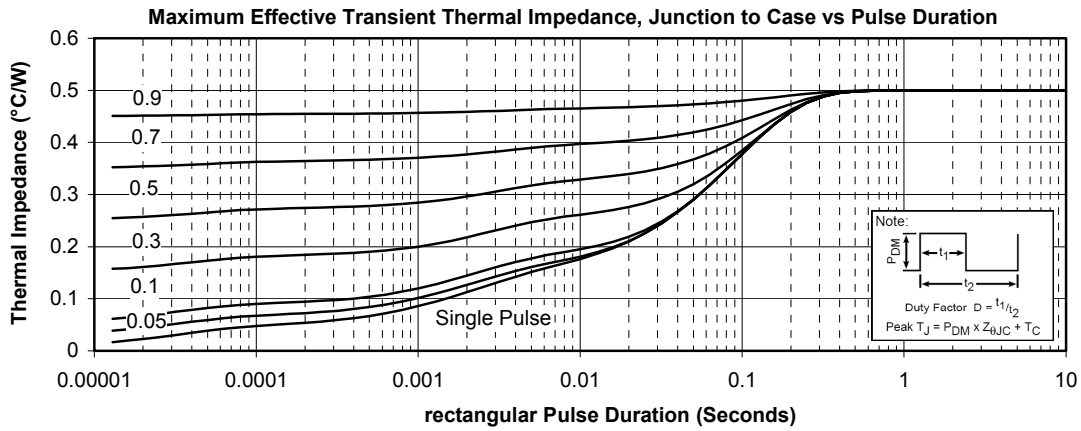
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

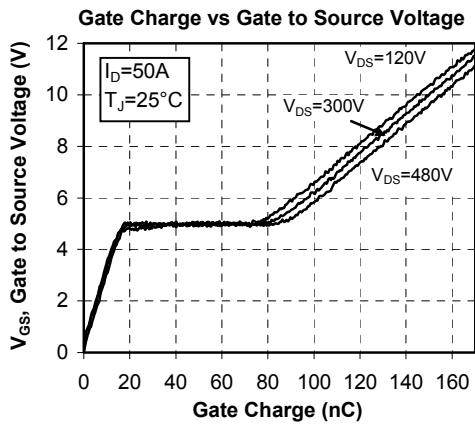
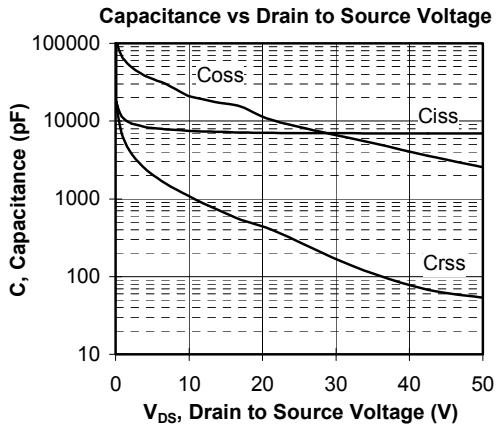
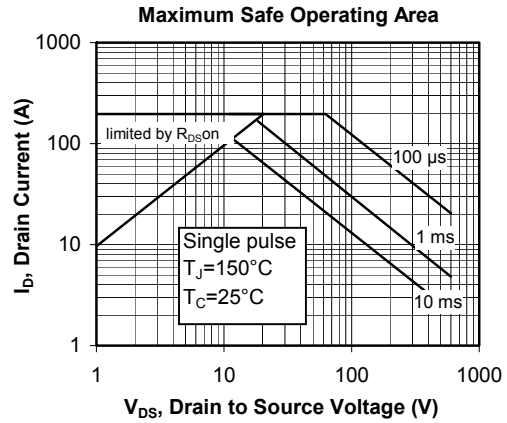
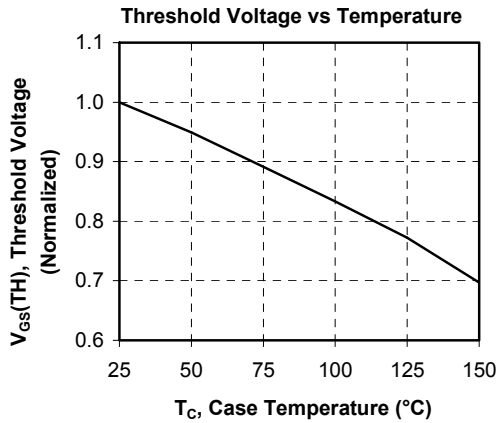
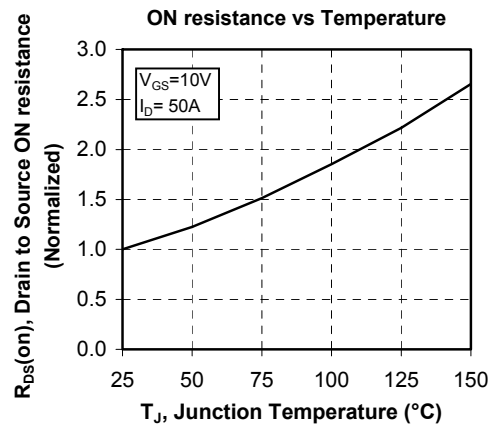
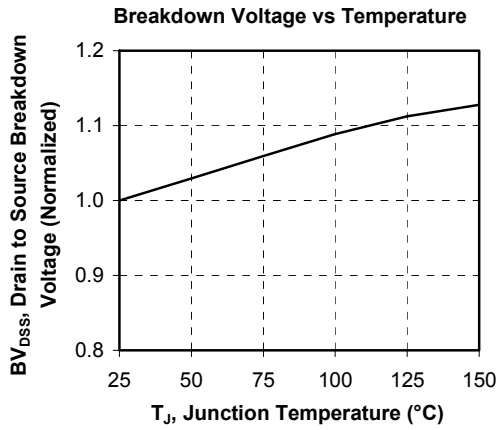
T: Thermistor temperature
 R_T: Thermistor value at T

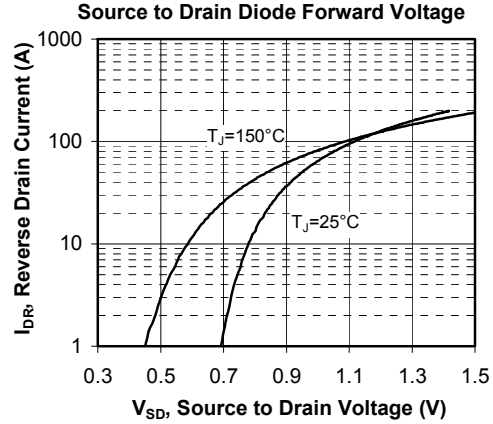
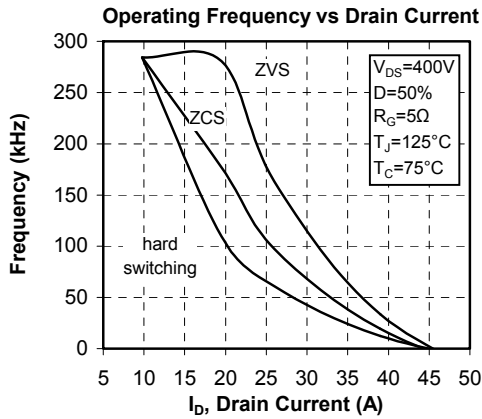
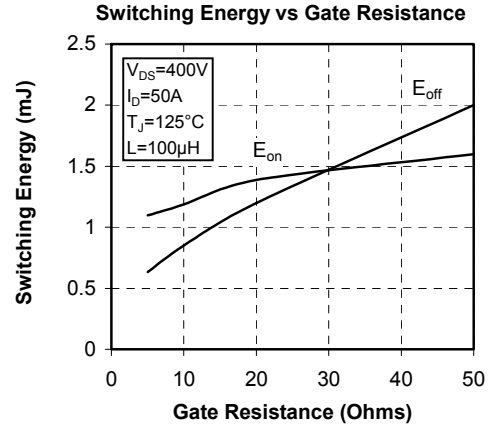
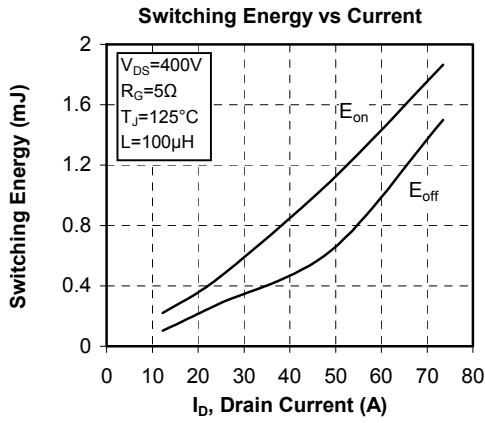
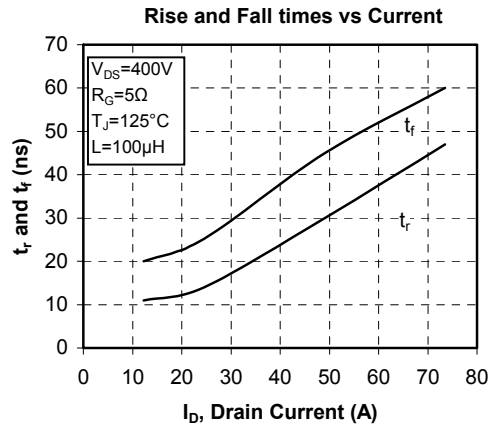
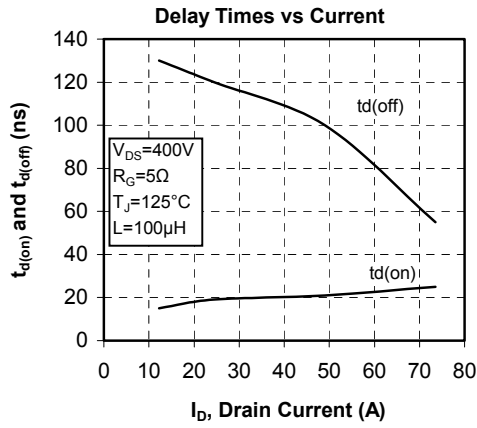
SP1 Package outline (dimensions in mm)


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

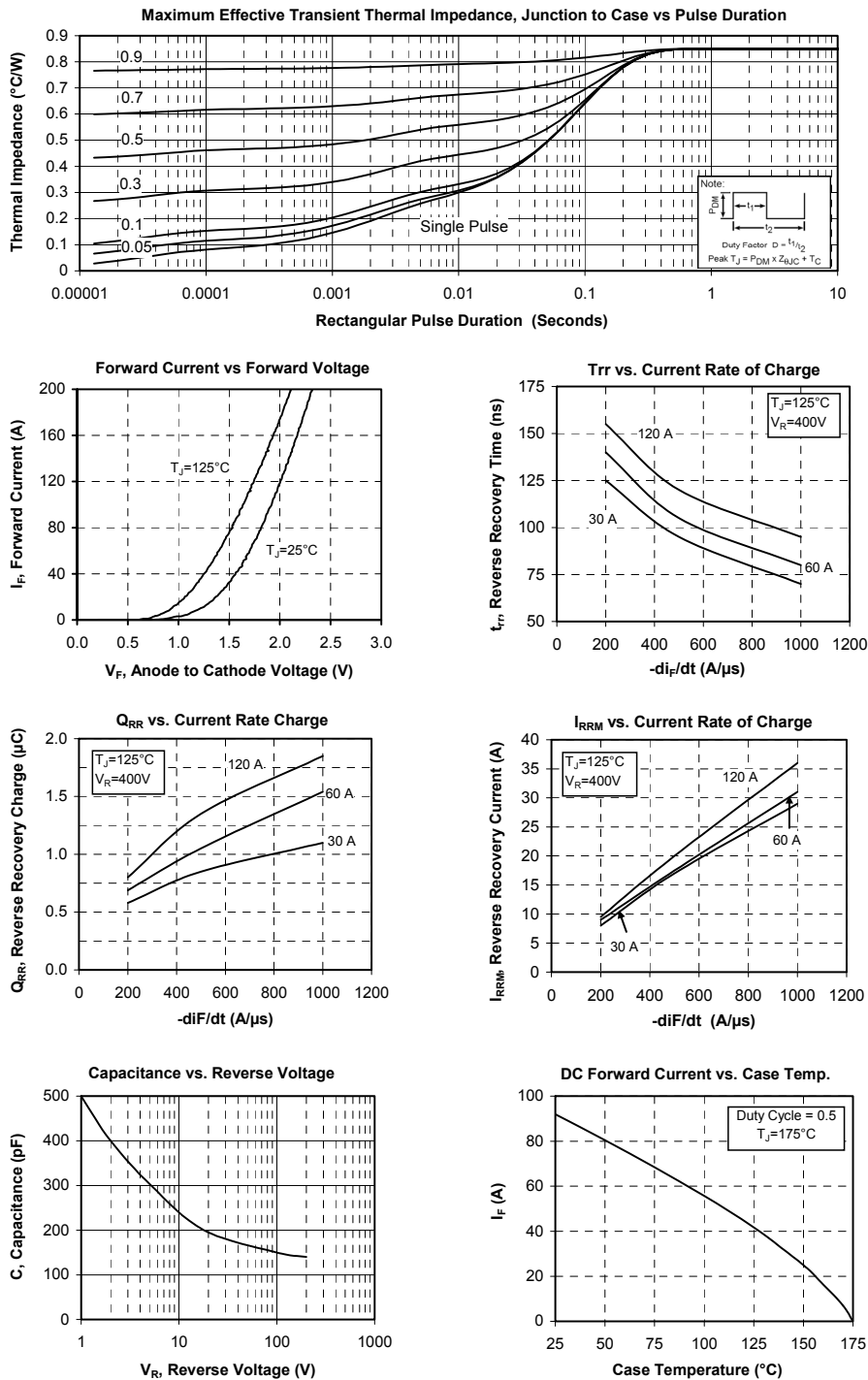
Typical CoolMOS Performance Curve







Typical chopper diode Performance Curve



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